



PTR928

PNP Epitaxial Silicon Transistor
-3 Amperes / 10 Watts

Audio Frequency Power Amplifier

- Low speed switching
- Complement to PTR882



Absolute Maximum Ratings

TC=25°C unless otherwise noted

CHARACTERISTICS	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-55	V
Emitter-Base Voltage	V_{EBO}	-7	V
Collector Current (DC)	I_C	-3	A
Collector Current (Pulse)	I_{CP}	-7	A
Base Current	I_B	-0.6	A
Collector Dissipation (Tc=25°C) (Ta=25°C)	P_C	10	W
		1	
Junction to Ambient	$R_{\theta ja}$	132	°C/W
Junction to Case	$R_{\theta jc}$	13.5	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-65~150	°C

* Pulse Test: Pulse Width≤10ms, Duty Cycles≤50%

Electrical Characteristics

TC=25°C unless otherwise noted

CHARACTERISTICS	SYMBOL	Test Condition	Min	Typ.	Max	Unit
Collector Cut-off Current	I_{CBO}	$V_{CB}=-60V, I_E=0$			-1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-1	μA
*DC Current Gain	h_{FE}	$V_{CE}=-2V, I_C=-1A$	140		320	
*Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-2A, I_B=-0.2A$		-0.4	-0.55	V
*Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-2A, I_B=-0.2A$		-1.0	-1.5	V
Output Capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=0.1MHz$		48		pF
Current Gain Bandwidth Product	f_T	$V_{CE}=-5V, I_E=-0.1A$		120		MHz

* Pulse Test: Pulse Width≤250μs, Duty Cycles≤2%

Typical Characteristics

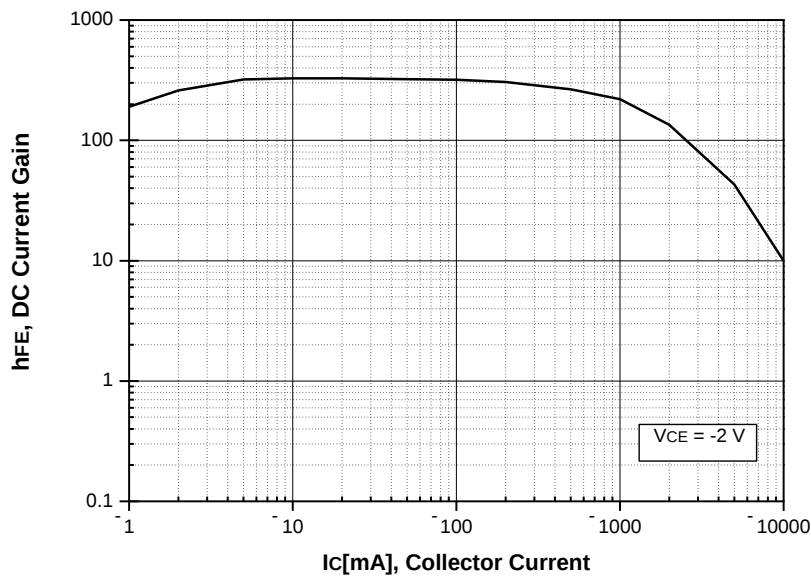


Figure 1. DC Current Gain

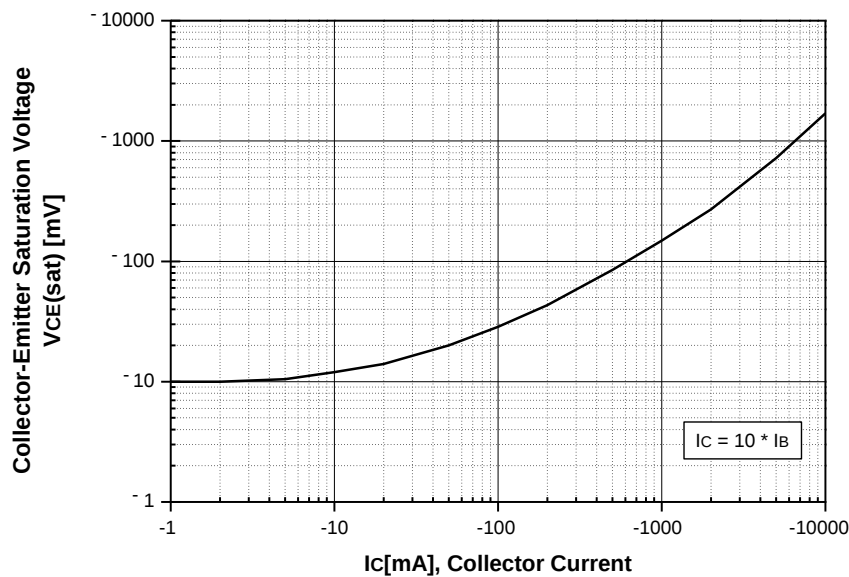


Figure 2. Collector-Emitter Saturation Voltage

Typical Characteristics

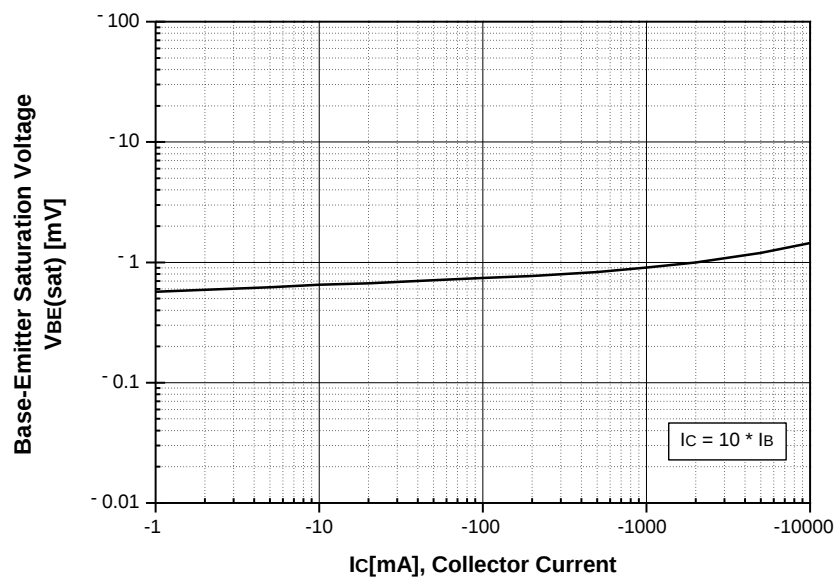


Figure 3. Base-Emitter Saturation Voltage

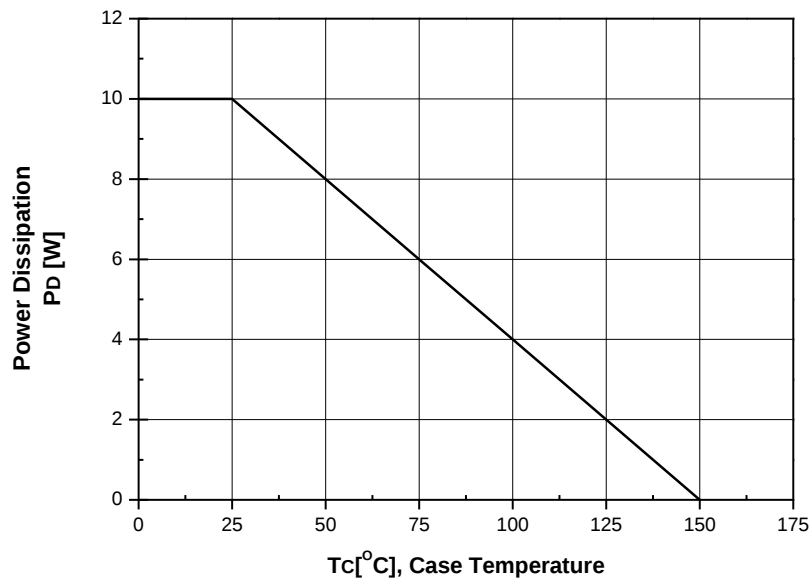


Figure 4. Power Derating